[Claims]

[Claim 1]

A semiconductor device comprising:

a stacked body including a first electrode layer and a second electrode layer provided to be electrically insulated from the first electrode layer in a stacking direction;

at least two first insulating layers provided in the stacked body to penetrate from an upper end of the stacked body to a lower end of the stacked body, and extending in a first direction intersecting the stacking direction;

a first staircase portion provided in a first end region of the stacked body between the at least two first insulating layers;

a second staircase portion provided in a second end region of the stacked body located on a side opposite to the first end region between the at least two first insulating layers; and

a second insulating layer extending in the first direction, provided in the stacked body between the at least two first insulating layers, and dividing the second electrode layer in the first direction,

a length in the first direction of the second insulating layer being longer than a length in the first direction of the second electrode layer and shorter than a length in the first direction of the first electrode layer, and

the first electrode layer is a dummy word line.

[Claim 2]

The device according to claim 1, wherein

the second electrode layer is a selection gate layer.

[Claim 3]

The device according to claim 1, wherein

the stacked body includes a first column-shaped portion provided in an intermediate region of the stacked body located between the first end region and the second end region, the first

column-shaped portion extending in the stacking direction, and

the first column-shaped portion includes:

a semiconductor body extending in the stacking direction; and

a charge storage portion provided between the semiconductor body and the first electrode layer.